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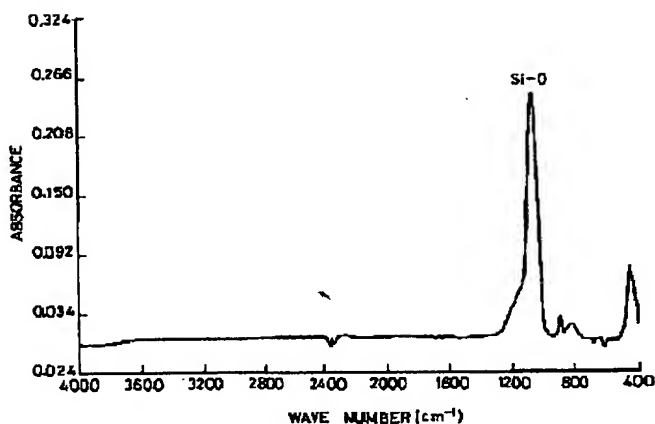
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APPLICANT : KAWASAKI STEEL CORP;

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TITLE : METHOD FOR FORMING
SEMICONDUCTOR FILM



ABSTRACT : PURPOSE: To provide a method for forming a semiconductor film, wherein an oxide film having a good flatness and a good film quality can be formed even on a surface of a high aspect ratio.

CONSTITUTION: A method for forming a semiconductor film, wherein a silicon oxide film is formed by a chemical vapor growth method through using as its raw material gas the gas obtained by adding a compound containing oxygen to the organic silane compound specified by a general chemical formula $(R_1 R_2 N)_n SiH_{4-n}$ (in the formula, each of R_1 , R_2 is one of H -, CH_3 -, C_2H_5 -, C_3H_7 -, C_4H_9 -, and at least one of R_1 , R_2 is not H -, and n is one of integers 1-4.).

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